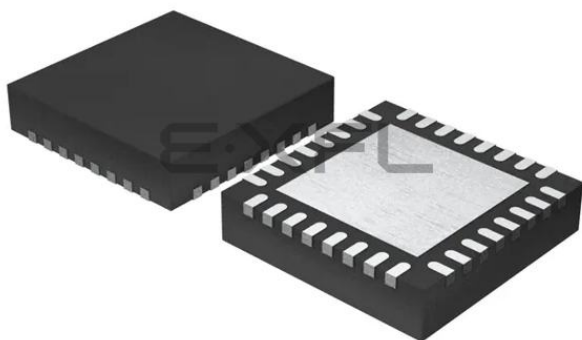




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I ² C, LINbus, SPI, TSI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	28
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D - 16bit; D/A - 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount, Wettable Flank
Package / Case	32-VFQFN Exposed Pad
Supplier Device Package	32-HVQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl16z128vm4

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3.13 16-bit sigma delta analog-to-digital converters (SDADC)

Three 16-bit sigma-delta analog-to-digital converters are embedded in the STM32F373xx. They have up to two separate supply voltages allowing the analog function voltage range to be independent from the STM32F373xx power supply. They share up to 21 input pins which may be configured in any combination of single-ended (up to 21) or differential inputs (up to 11).

The conversion speed is up to 16.6 ksps for each SDADC when converting multiple channels and up to 50 ksps per SDADC if single channel conversion is used. There are two conversion modes: single conversion mode or continuous mode, capable of automatically scanning any number of channels. The data can be automatically stored in a system RAM buffer, reducing the software overhead.

A timer triggering system can be used in order to control the start of conversion of the three SDADCs and/or the 12-bit fast ADC. This timing control is very flexible, capable of triggering simultaneous conversions or inserting a programmable delay between the ADCs.

Up to two external reference pins (VREFSD+, VREFSD-) and an internal 1.2/1.8 V reference can be used in conjunction with a programmable gain (x0.5 to x32) in order to fine-tune the input voltage range of the SDADC. VREFSD - pin is used as negative signal reference in case of single-ended input mode.

3.14 Digital-to-analog converter (DAC)

The devices feature two 12-bit buffered DACs with three output channels that can be used to convert three digital signals into three analog voltage signal outputs. The internal structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This digital Interface supports the following features:

- Two DAC converters with three output channels:
 - DAC1 with two output channels
 - DAC2 with one output channel.
- 8-bit or 10-bit monotonic output
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation (DAC1 only)
- Triangular wave generation (DAC1 only)
- Dual DAC channel independent or simultaneous conversions (DAC1 only)
- DMA capability for each channel
- External triggers for conversion

3.21 Serial peripheral interface (SPI)/Inter-integrated sound interfaces (I²S)

Three SPIs are able to communicate at up to 18 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The SPIs can be served by the DMA controller.

Three standard I²S interfaces (multiplexed with SPI1, SPI2 and SPI3) are available, that can be operated in master or slave mode. These interfaces can be configured to operate with 16/32 bit resolution, as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I²S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency. All I2S interfaces can operate in half-duplex mode only.

Refer to [Table 9](#) for the features between SPI1, SPI2 and SPI3.

Table 9. STM32F373xx SPI/I2S implementation

SPI features ⁽¹⁾	SPI1	SPI2	SPI3
Hardware CRC calculation	X	X	X
Rx/Tx FIFO	X	X	X
NSS pulse mode	X	X	X
I2S mode	X	X	X
TI mode	X	X	X
I2S full-duplex mode	-	-	-

1. X = supported.

3.22 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)

The device embeds a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory overhead. It has a clock domain independent from the CPU clock, allowing the HDMI_CEC controller to wakeup the MCU from Stop mode on data reception.

3.23 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

3.24 Universal serial bus (USB)

The STM32F373xx embeds an USB device peripheral compatible with the USB full-speed 12 Mbs. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and suspend/resume support. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

3.25 Serial wire JTAG debug port (SWJ-DP)

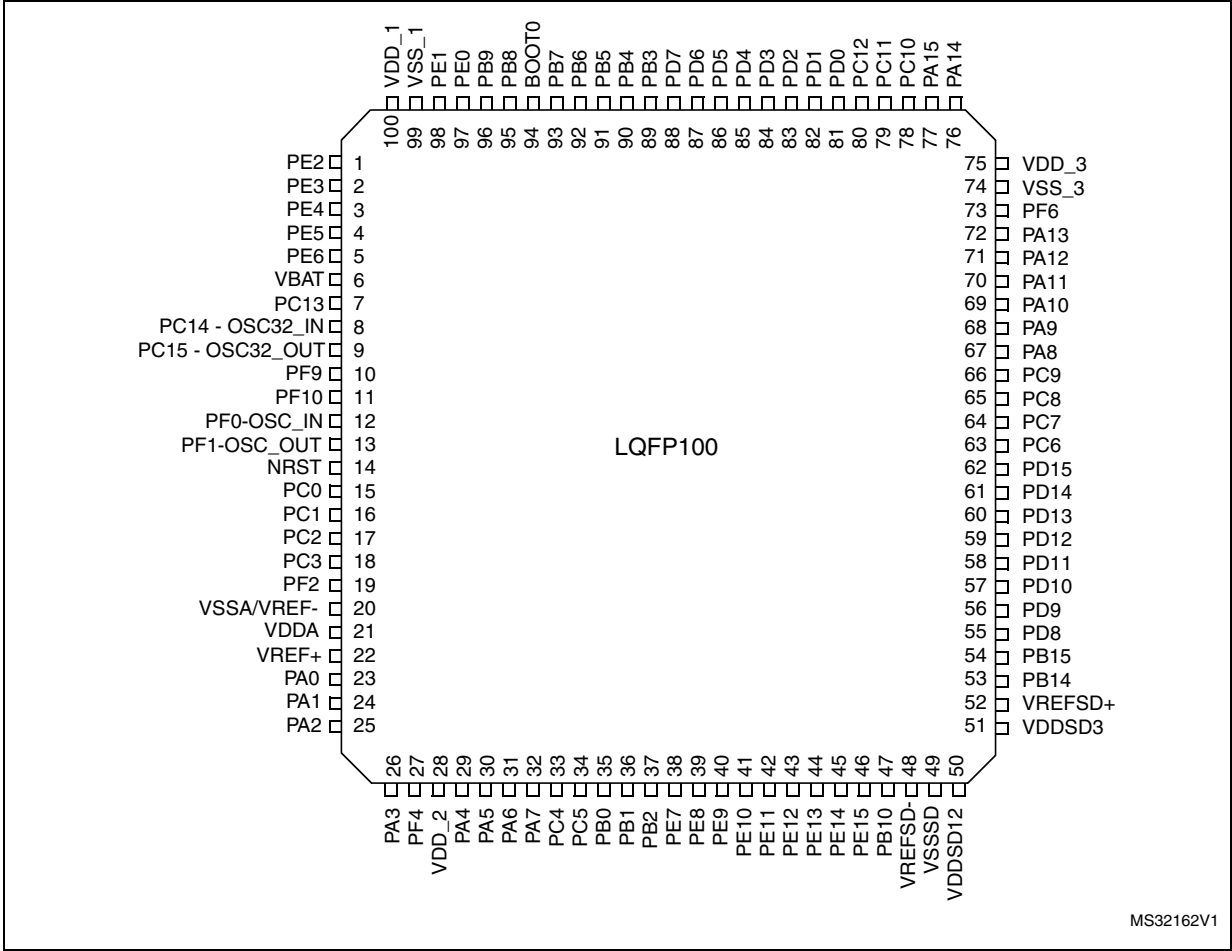
The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

3.26 Embedded trace macrocell™

The ARM embedded trace macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F373xx through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using USB, Ethernet, or any other high-speed channel. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer running debugger software. TPA hardware is commercially available from common development tool vendors. It operates with third party debugger software tools.

Figure 4. STM32F373xx LQFP100 pinout



MS32162V1

Table 10. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input only pin
		I/O	Input / output pin
I/O structure		FT	5 V tolerant I/O
		FTf	5 V tolerant I/O, FM+ capable
		TTa	3.3 V tolerant I/O directly connected to ADC
		TC	Standard 3.3 V I/O
		B	Dedicated BOOT0 pin
		RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes		Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

Table 11. STM32F373xx pin definitions

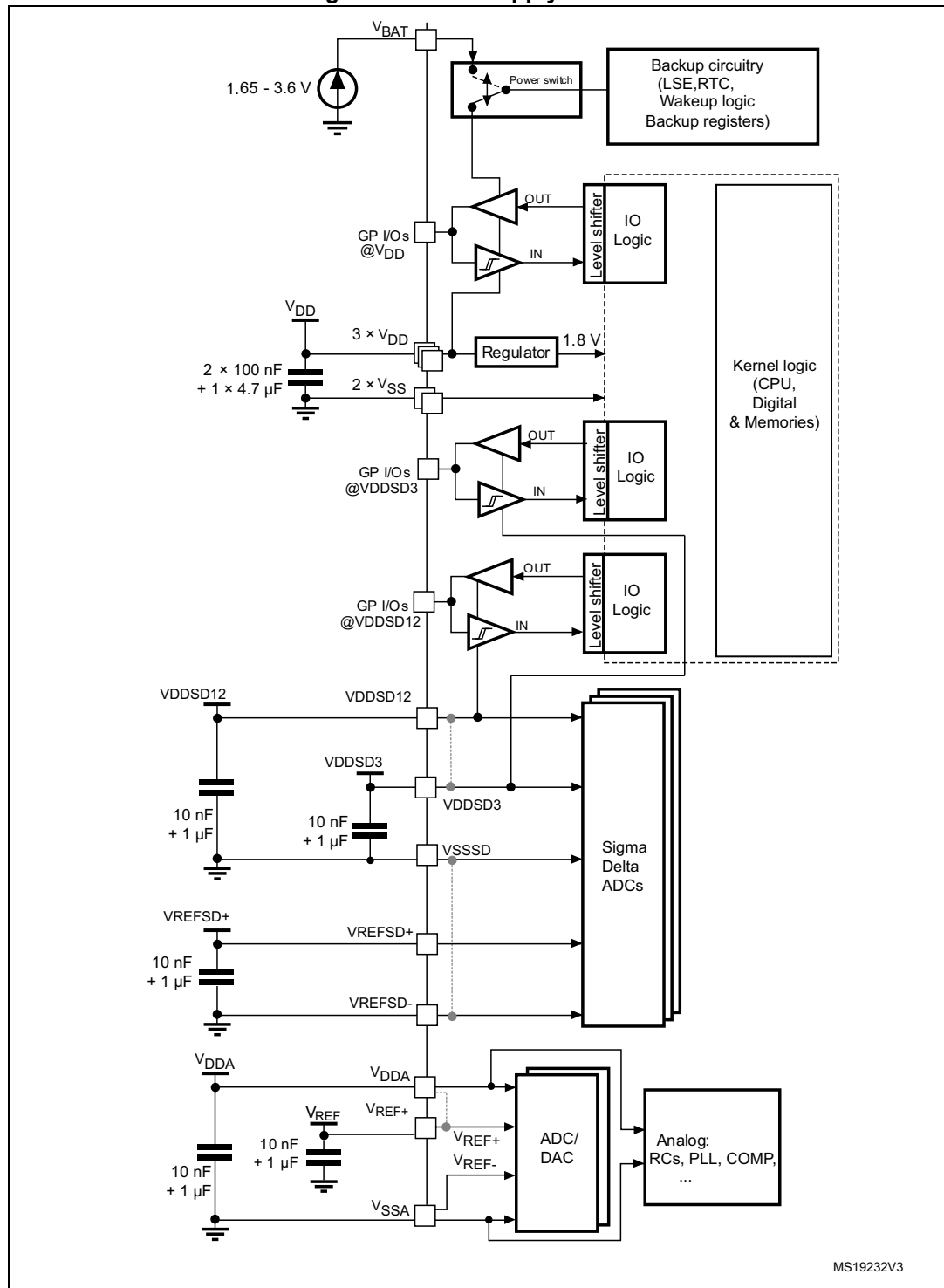
Pin numbers				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP100	UFBGA100	LQFP64	LQFP48					Alternate function	Additional functions
1	B2	-	-	PE2	I/O	FT	(2)	TSC_G7_IO1, TRACECLK	-
2	A1	-	-	PE3	I/O	FT	(2)	TSC_G7_IO2, TRACED0	-
3	B1	-	-	PE4	I/O	FT	(2)	TSC_G7_IO3, TRACED1	-
4	C2	-	-	PE5	I/O	FT	(2)	TSC_G7_IO4, TRACED2	-
5	D2	-	-	PE6	I/O	FT	(2)	TRACED3	WKUP3, RTC_TAMPER3
6	E2	1	1	VBAT	S	-	-	Backup power supply	
7	C1	2	2	PC13 ⁽¹⁾	I/O	TC	-	-	WKUP2, ALARM_OUT, CALIB_OUT, TIMESTAMP, RTC_TAMPER1

Table 11. STM32F373xx pin definitions (continued)

Pin numbers				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP100	UFBGA100	LQFP64	LQFP48					Alternate function	Additional functions
51	L12	-	-	VDDSD3	S	-	(2)	SDADC3 power supply	
52	K12	33	25	VREFSD+	S	-	-	External reference voltage for SDADC1, SDADC2, SDADC3 (positive input)	
53	K11	34	26	PB14	I/O	TC	(4)	SPI2_MISO/I2S2_MCK, USART3_RTS, TIM15_CH1, TIM12_CH1, TSC_G6_IO1	SDADC3_AIN8P
54	K10	35	27	PB15	I/O	TC	(4)	SPI2_MOSI/I2S2_SD, TIM15_CH1N, TIM15_CH2, TIM12_CH2, TSC_G6_IO2, RTC_REFIN	SDADC3_AIN7P, SDADC3_AIN8M
55	K9	36	28	PD8	I/O	TC	(4)	SPI2_SCK/I2S2_CK, USART3_TX, TSC_G6_IO3	SDADC3_AIN6P
56	K8	-	-	PD9	I/O	TC	(4) (2)	USART3_RX, TSC_G6_IO4	SDADC3_AIN5P, SDADC3_AIN6M
57	J12	-	-	PD10	I/O	TC	(4) (2)	USART3_CK	SDADC3_AIN4P
58	J11	-	-	PD11	I/O	TC	(4) (2)	USART3_CTS	SDADC3_AIN3P, SDADC3_AIN4M
59	J10	-	-	PD12	I/O	TC	(4) (2)	USART3_RTS, TIM4_CH1, TSC_G8_IO1	SDADC3_AIN2P
60	H12	-	-	PD13	I/O	TC	(4) (2)	TIM4_CH2, TSC_G8_IO2	SDADC3_AIN1P, SDADC3_AIN2M
61	H11	-	-	PD14	I/O	TC	(4) (2)	TIM4_CH3, TSC_G8_IO3	SDADC3_AIN0P
62	H10	-	-	PD15	I/O	TC	(4) (2)	TIM4_CH4, TSC_G8_IO4	SDADC3_AIN0M
63	E12	37	-	PC6	I/O	FT	(2)	TIM3_CH1, SPI1_NSS/I2S1_WS	-
64	E11	38	-	PC7	I/O	FT	(2)	TIM3_CH2, SPI1_SCK/I2S1_CK,	-
65	E10	39	-	PC8	I/O	FT	(2)	SPI1_MISO/I2S1_MCK, TIM3_CH3	-
66	D12	40	-	PC9	I/O	FT	(2)	SPI1_MOSI/I2S1_SD, TIM3_CH4	-

6.1.6 Power supply scheme

Figure 9. Power supply scheme



1. Dotted lines represent the internal connections on low pin count packages, joining the dedicated supply pins.

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 10: Current consumption measurement scheme](#).

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states from 48 MHz to 72 MHz)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{APB1} = f_{AHB}/2$, $f_{APB2} = f_{AHB}$
- When $f_{HCLK} > 8$ MHz PLL is ON and PLL inputs is equal to $HSI/2 = 4$ MHz (if internal clock is used) or HSE = 8 MHz (if HSE bypass mode is used)

The parameters given in [Table 28](#) to [Table 34](#) are derived from tests performed under ambient temperature and supply voltage conditions summarized in [Table 22](#).

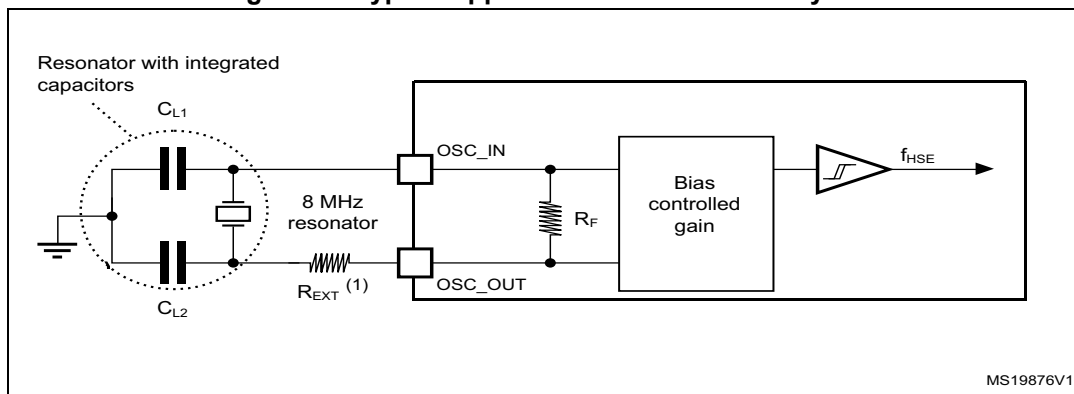
Table 28. Typical and maximum current consumption from V_{DD} supply at $V_{DD} = 3.6$ V⁽¹⁾

Symbol	Parameter	Conditions	f _{HCLK}	All peripherals enabled				All peripherals disabled				Unit
				Typ	Max @ T _A ⁽²⁾			Typ	Max @ T _A ⁽²⁾			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I _{DD}	Supply current in Run mode, code executing from Flash	HSE bypass, PLL on	72 MHz	63.1	70.7	71.5	73.4	29.2	31.1	31.7	34.2	mA
			64 MHz	56.3	63.3	64.1	64.9	26.1	27.8	28.4	30.4	
			48 MHz	42.5	48.5	48.0	50.1	19.9	22.6	21.9	23.1	
			32 MHz	28.8	31.4	32.2	34.3	13.1	16.1	14.9	16.2	
			24 MHz	21.9	24.4	24.4	25.8	10.1	10.9	11.9	12.4	
		HSE bypass, PLL off	8 MHz	7.3	8.0	9.3	9.3	3.7	4.1	4.4	5.0	
			1 MHz	1.1	1.5	1.8	2.3	0.8	1.1	1.4	1.9	
		HSI clock, PLL on	64 MHz	51.7	57.7	58.0	60.4	25.8	27.6	28.1	30.1	
			48 MHz	38.6	45.9	43.5	46.9	19.8	21.9	21.7	22.8	
			32 MHz	26.4	31.1	29.7	31.9	13.1	15.7	14.8	16.2	
			24 MHz	20.3	22.6	22.6	23.7	6.9	7.5	8.1	8.8	
		HSI clock, PLL off	8 MHz	7.0	7.6	8.8	8.8	3.7	4.1	4.4	5.0	

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 14](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note: For information on electing the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 14. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 48. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{HCLK}]	Unit
				8/72 MHz	
S _{EMI}	Peak level	V _{DD} - 3.3 V, T _A - 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	9	dBμV
			30 to 130 MHz	26	
			130 MHz to 1 GHz	30	
			SAE EMI Level	4	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 49. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to JESD22-A114	2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to ANSI/ESD STM5.3.1, LQFP100, LQFP64, LQFP48 and UFBGA100 packages	II	500	

1. Guaranteed by characterization results.

2. ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 6.3.14](#) does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA} , frequency and temperature ranges.
4. Guaranteed by characterization results.

Figure 27. ADC accuracy characteristics

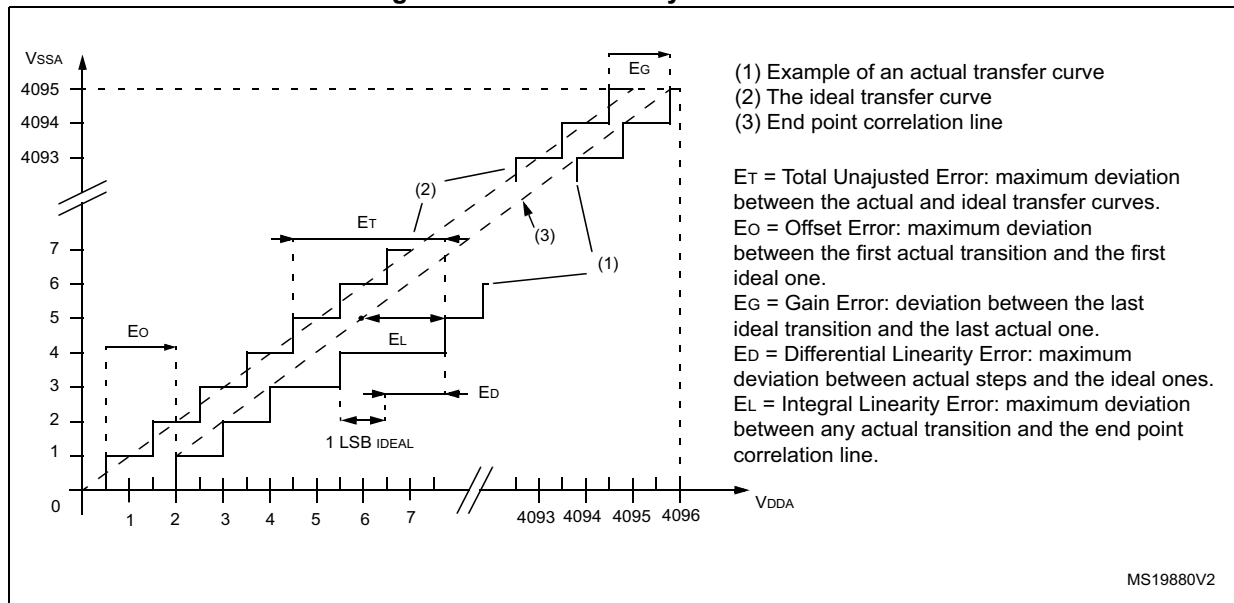
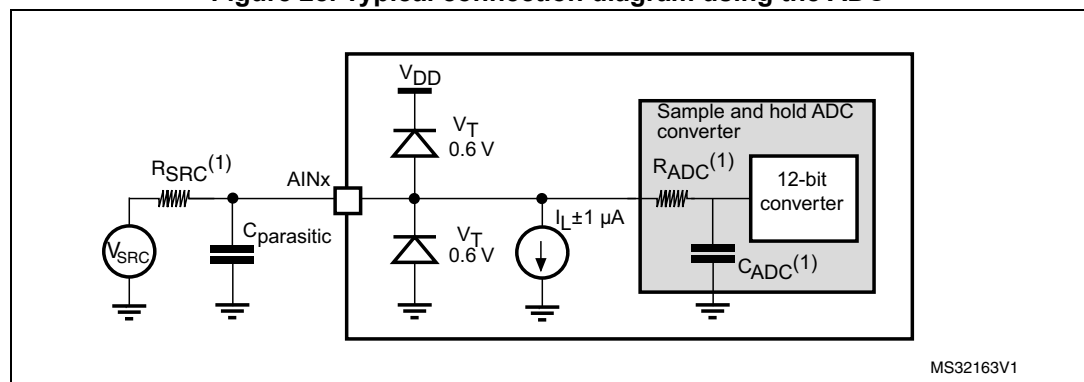


Figure 28. Typical connection diagram using the ADC



1. Refer to [Table 60](#) for the values of R_{SRC} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

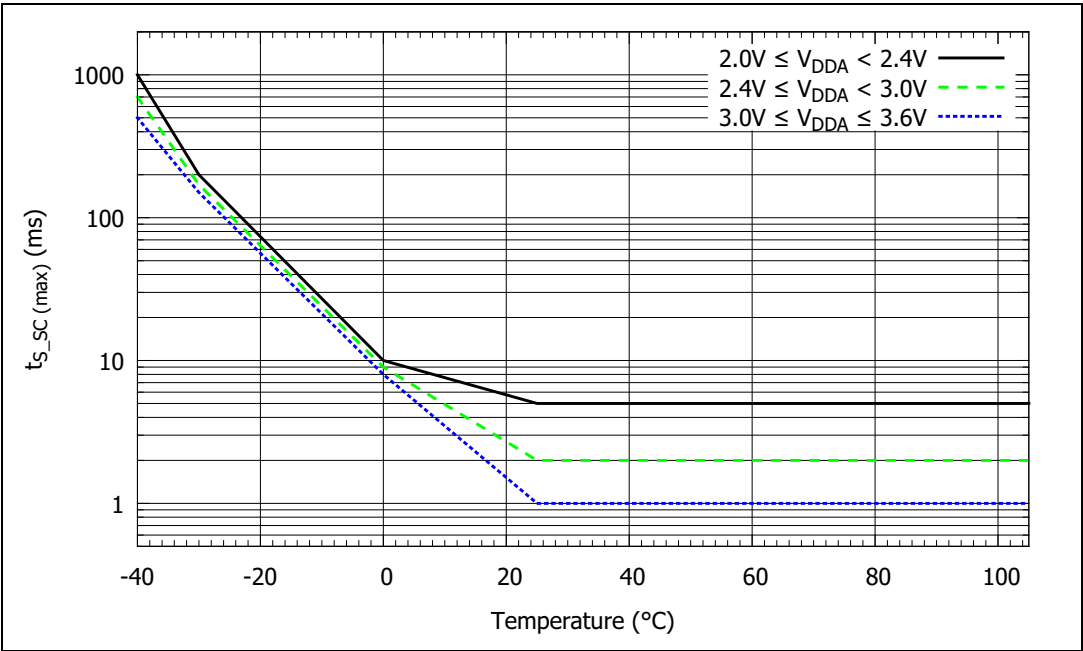
Power supply decoupling should be performed as shown in [Figure 9](#). The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

Table 64. Comparator characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max ⁽¹⁾	Unit
V_{hys}	Comparator hysteresis	No hysteresis (COMPxHYST[1:0]=00)	-	-	0	-	mV
		Low hysteresis (COMPxHYST[1:0]=01)	High speed mode	3	8	13	
			All other power modes	5		10	
		Medium hysteresis (COMPxHYST[1:0]=10)	High speed mode	7	15	26	
			All other power modes	9		19	
		High hysteresis (COMPxHYST[1:0]=11)	High speed mode	18	31	49	
			All other power modes	19		40	

- 1. Guaranteed by design.
- 2. For more details and conditions see [Figure 30: Maximum VREFINT scaler startup time from power down](#)

Figure 30. Maximum V_{REFINT} scaler startup time from power down



6.3.23 USB characteristics

Table 71. USB startup time

Symbol	Parameter	Max	Unit
$t_{\text{STARTUP}}^{(1)}$	USB transceiver startup time	1	μs

1. Guaranteed by design.

Table 72. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min. ⁽¹⁾	Max. ⁽¹⁾	Unit
Input levels					
V _{DD}	USB operating voltage ⁽²⁾	-	3.0 ⁽³⁾	3.6	V
V _{DI} ⁽⁴⁾	Differential input sensitivity (for USB compliance)	I(USB_DP, USB_DM)	0.2	-	V
V _{CM} ⁽⁴⁾	Differential common mode range	Includes V _{DI} range	0.8	2.5	
V _{SE} ⁽⁴⁾	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V _{OL}	Static output level low	R _L of 1.5 kΩ to 3.6 V ⁽⁵⁾	-	0.3	V
V _{OH}	Static output level high	R _L of 15 kΩ to V _{SS} ⁽⁵⁾	2.8	3.6	

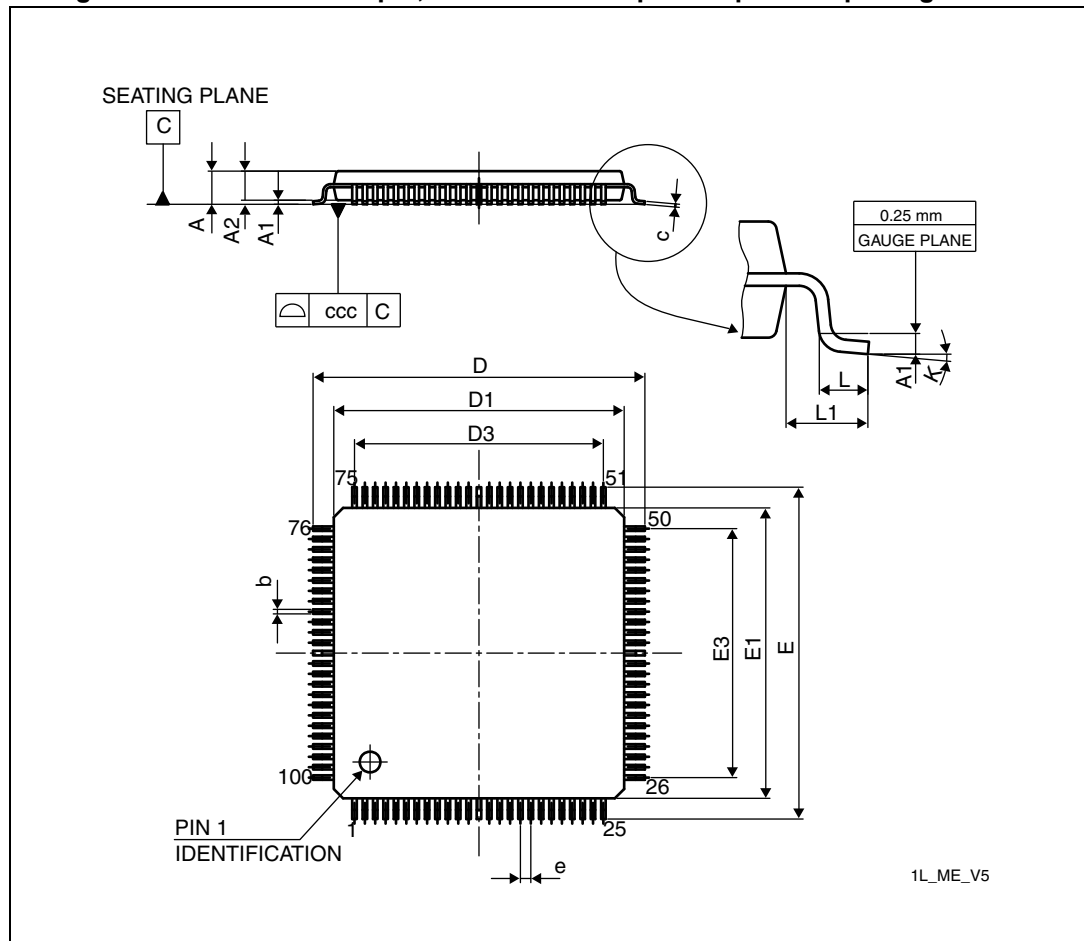
1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 k Ω resistor to a 3.0-to-3.6 V voltage range.
3. The STM32F3xxx USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
4. Guaranteed by design.
5. R_{L} is the load connected on the USB drivers

Table 74. SDADC characteristics (continued)⁽¹⁾

Symbol	Parameter	Conditions				Min	Typ	Max	Unit	Note	
EO	Offset error	Differential mode	gain = 1	f _{ADC} = 1.5 MHz	V _{DDSDx} = 3.3	V _{REFSD+} = 3.3	-	-	110	uV	after offset calibration
				f _{ADC} = 6 MHz		V _{REFSD+} = 1.2	-	-	110		
						V _{REFSD+} = 3.3	-	-	100		
			gain = 8	f _{ADC} = 6 MHz		V _{REFSD+} = 1.2	-	-	70		
						V _{REFSD+} = 3.3	-	-	100		
				f _{ADC} = 1.5 MHz		V _{REFSD+} = 3.3	-	-	90		
		Single ended mode	gain = 1	-		V _{REFSD+} = 1.2	-	-	2100		
						V _{REFSD+} = 3.3	-	-	2000		
			gain = 8			V _{REFSD+} = 1.2	-	-	1500		
						V _{REFSD+} = 3.3	-	-	1800		
D _{voffsettemp}	Offset drift with temperature	Differential or single ended mode, gain = 1, V _{DDSDx} = 3.3 V				-	10	15	uV/K	-	
EG	Gain error	All gains, differential mode, single ended mode				-2.4	-2.7	-3.1	%	negative gain error = data result are greater than ideal	
EGT	Gain drift with temperature	gain = 1, differential mode, single ended mode				-	0	-	ppm /K	-	

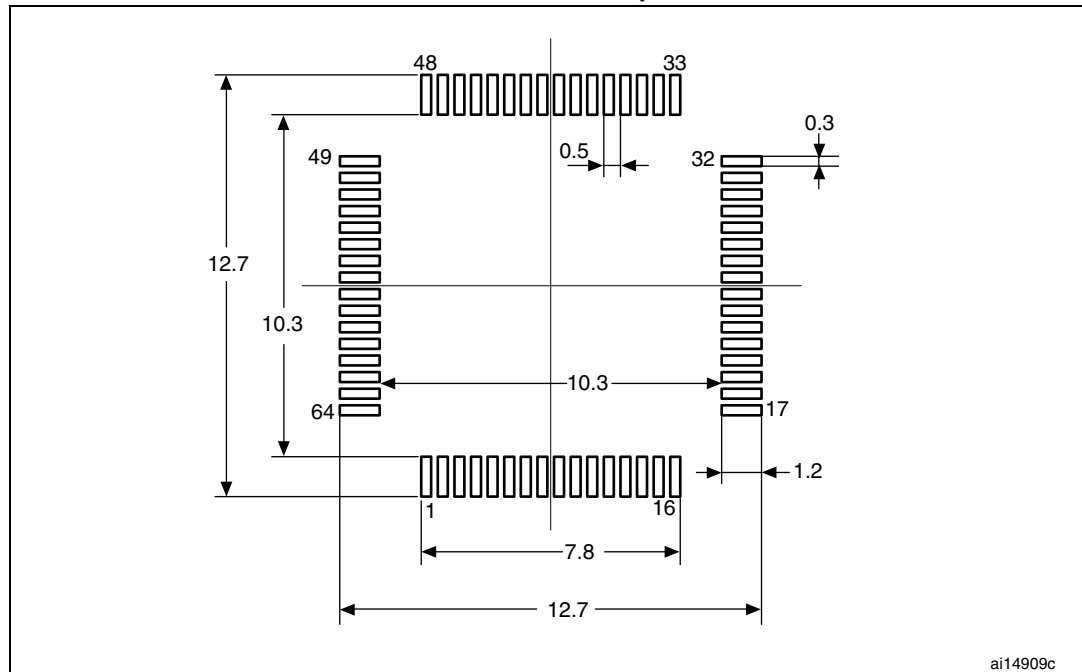
7.2 LQFP100 package information

Figure 35. LQFP100 - 100-pin, 14 x 14 mm low-profile quad flat package outline



1. Drawing is not to scale.

Figure 39. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint

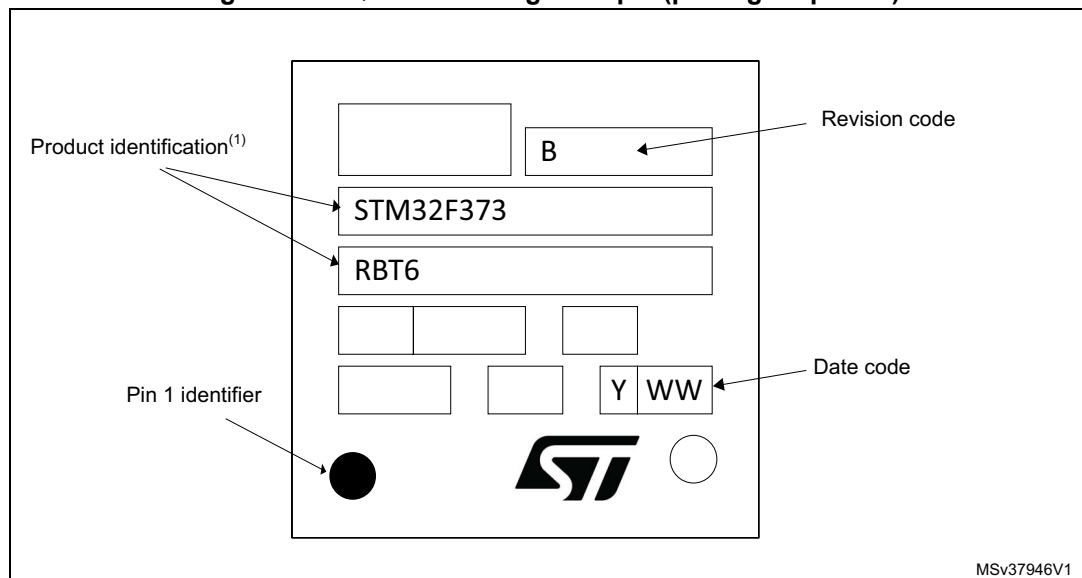


1. Dimensions are expressed in millimeters.

Device marking for LQFP64

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 40. LQFP64 marking example (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.5.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in [Section 8: Part numbering](#).

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F373xx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature $T_{Amax} = 82\text{ °C}$ (measured according to JESD51-2),
 $I_{DDmax} = 50\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 3 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$ and maximum 2 I/Os used at the same time in output at low level with $I_{OL} = 20\text{ mA}$, $V_{OL} = 1.3\text{ V}$

$$P_{INTmax} = 50\text{ mA} \times 3.5\text{ V} = 175\text{ mW}$$

$$P_{IOmax} = 3 \times 8\text{ mA} \times 0.4\text{ V} + 2 \times 20\text{ mA} \times 1.3\text{ V} = 61.6\text{ mW}$$

This gives: $P_{INTmax} = 175\text{ mW}$ and $P_{IOmax} = 61.6\text{ mW}$:

$$P_{Dmax} = 175 + 61.6 = 236.6\text{ mW}$$

Thus: $P_{Dmax} = 236.6\text{ mW}$

Using the values obtained in [Table 81](#) T_{Jmax} is calculated as follows:

– For LQFP64, 45°C/W

$$T_{Jmax} = 82\text{ °C} + (45\text{ °C/W} \times 236.6\text{ mW}) = 82\text{ °C} + 10.65\text{ °C} = 92.65\text{ °C}$$

This is within the range of the suffix 6 version parts ($-40 < T_J < 105\text{ °C}$).

In this case, parts must be ordered at least with the temperature range suffix 6 (see [Section 8: Part numbering](#)).

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature $T_{Amax} = 115\text{ °C}$ (measured according to JESD51-2),
 $I_{DDmax} = 20\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 9 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$

$$P_{INTmax} = 20\text{ mA} \times 3.5\text{ V} = 70\text{ mW}$$

$$P_{IOmax} = 9 \times 8\text{ mA} \times 0.4\text{ V} = 28.8\text{ mW}$$

This gives: $P_{INTmax} = 70\text{ mW}$ and $P_{IOmax} = 28.8\text{ mW}$:

$$P_{Dmax} = 70 + 28.8 = 98.8\text{ mW}$$

Thus: $P_{Dmax} = 98.8\text{ mW}$

8 Part numbering

For a list of available options (memory, package, and so on) or for further information on any aspect of this device, please contact your nearest ST sales office.

Table 82. Ordering information scheme

Example:	STM32	F	373	R	8	T	6	x								
Device family																
STM32 = ARM-based 32-bit microcontroller																
Product type																
F = General-purpose																
Sub-family																
373 = STM32F373xx																
Pin count																
C = 48 pins																
R = 64 pins																
V = 100 pins																
Code size																
8 = 64 Kbytes of Flash memory																
B = 128 Kbytes of Flash memory																
C = 256 Kbytes of Flash memory																
Package																
T = LQFP																
H = BGA																
Temperature range																
6 = Industrial temperature range, −40 to 85 °C																
7 = Industrial temperature range, −40 to 105 °C																
Options																
xxx = programmed parts																
TR = tape and reel																

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